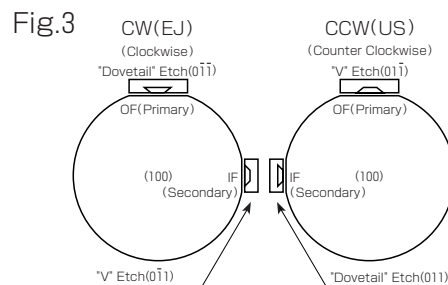
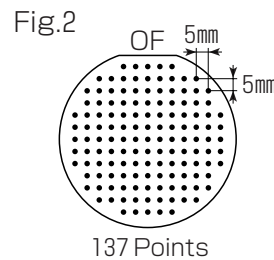
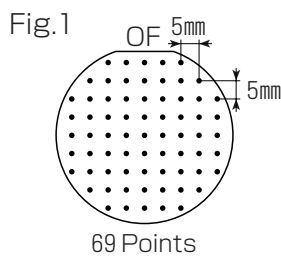


InP Single Crystal Wafers(p-Type)

Standard Specifications

Growth Method·Dopant	VCZ(*1)·Zn	
Carrier Concentration (cm ⁻³)	2~6×10 ¹⁸	
Resistivity (Ω·cm)	2~7×10 ⁻²	
Mobility (cm ² /V·sec)	35~80	
EPD Average (cm ⁻²)	≤5×10 ²	≤5×10 ³
EPD Guaranteed Area (*2)	100%	
Measuring Points of EPD	Fig.1	Fig.2
Diameter (mm)	50.0±0.3	76.0±0.3
OF (mm) (Fig.3) (*3)	16.0±1.0	22.0±1.0
IF (mm) (Fig.3)	7.0±1.0	12.0±1.0
Edge Rounding (mmR)	0.25 (Conform to SEMI Standards)	
Thickness (μm)	350±15	600±15
Orientation	(100) ±0.3°	
Surface Finish	P/LE	P/LE
	P/P	P/P
Surface Clean (*4)	EW	
Flatness·LPD (*5)	Refer to Page 8	
Package	Individual Container	



Notes

- (*1) VCZ : Vapor Pressure Controlled Czochralski
- (*2) EPD Guaranteed Area : Percentage of points within the spec.
- (*3) High Precision OF (±0.02°) is available for 2"φ.
- (*4) EW : Etched Wafer
- (*5) LPD : Light Point Defects

Attached Data

- Standard : Resistivity · Mobility · Diameter · OF · IF · Thickness (min.~max.)
EPD Map
- Option : Accuracy of Orientation · Flatness · Light Point Defects